



FZT1049A

#### 25V NPN MEDIUM POWER TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > 25V
- I<sub>C</sub> = 5A high Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 70mV @ 1A</li>
- $R_{CE(sat)} = 50m\Omega$  for a low equivalent On-Resistance
- h<sub>FE</sub> specified up to 20A for a high gain hold up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

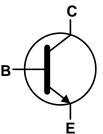
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
  Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

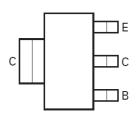
SOT223



Top View



Device Symbol



Top View Pin-Out

#### **Ordering Information** (Note 4)

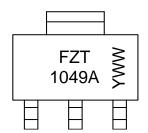
Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT1049ATA	AEC-Q101	FZT1049A	7	12	1,000
FZT1049ATC	AEC-Q101	FZT1049A	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

#### **Marking Information**

**SOT223** 



FZT 1049A = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



#### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	5	Α
Peak Pulse Current	I <sub>CM</sub>	20	Α

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Dawar Dissipation	(Note 6)	D	2.0	W	
Power Dissipation	(Note 7)	$P_D$	1.6		
	(Note 8)		1.2	1	
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	Б	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	10.9		
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

### ESD Ratings (Note 10)

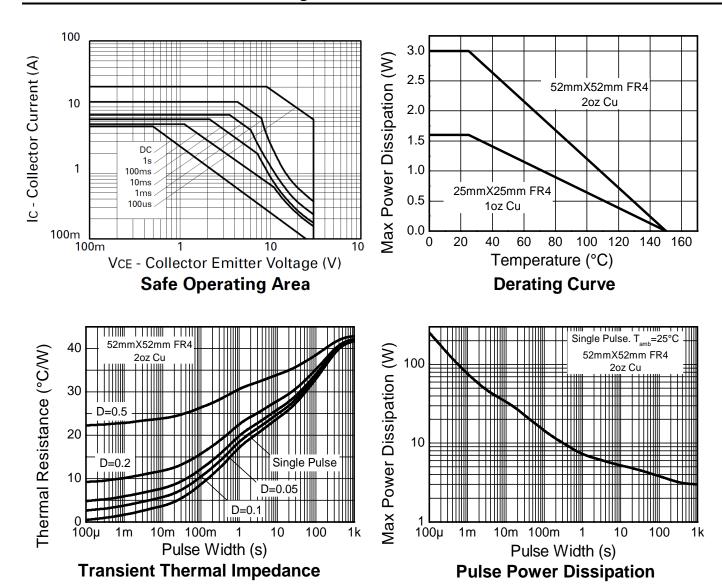
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

#### Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper. 8. Same as note (5), except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics and Derating Information**





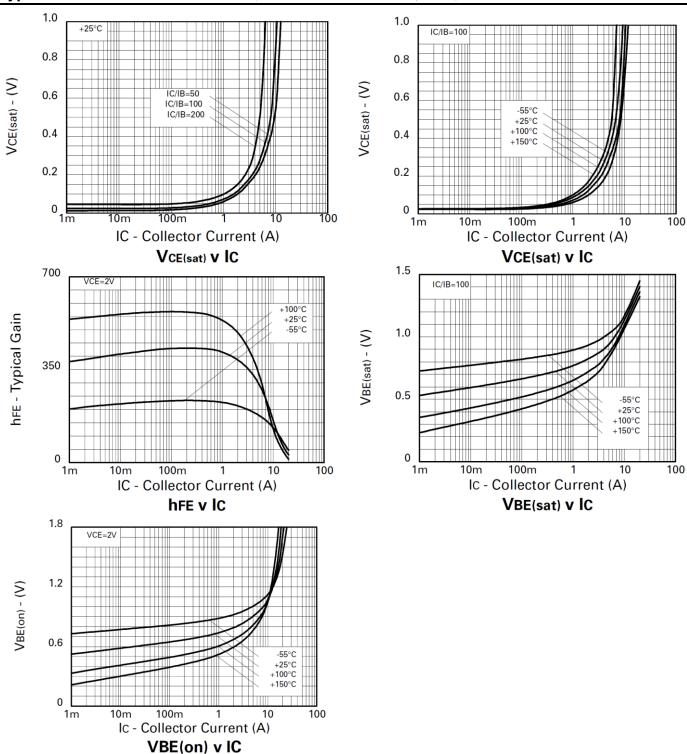
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	80	130	-	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 11)	$BV_CER$	80	130	-	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	25	30	-	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	9	-	V	I <sub>E</sub> = 100μA
Collector Cutoff Current	I <sub>CBO</sub>	-	0.3	10	nA	V <sub>CB</sub> = 35V
Emitter Cutoff Current	I <sub>EBO</sub>	-	0.3	10	nA	V <sub>EB</sub> = 4V
		280	440	-	-	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 2V
		300	450	-		$I_C = 0.5A, V_{CE} = 2V$
DC Current Transfer Static Ratio (Note 11)	h <sub>FE</sub>	300	450	1,200		$I_C = 1A$ , $V_{CE} = 2V$
		180	280	-		$I_C = -5A, V_{CE} = 2V$
		40	80	-		$I_C = 20A, V_{CE} = 2V$
		-	35	60	mV	$I_C = 0.5A, I_B = 10mA$
Callactor Emitter Seturation Voltage (Note 11)	<b>V</b>	-	70	100		$I_C = 1A, I_B = 10mA$
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	-	180	250		$I_C = 3A, I_B = 30mA$
		-	250	330		$I_C = 5A, I_B = 50mA$
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	-	950	1,050	mV	$I_C = 5A, I_B = 50mA$
Base-Emitter Turn-on Voltage (Note 11)	$V_{BE(on)}$	-	900	1,000	mV	I <sub>C</sub> = 5A, V <sub>CE</sub> = 2V
Transitional Frequency (Note 11)	f <sub>T</sub>	-	180	-	MHz	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 10V, f = 100MHz
Output Capacitance	C <sub>obo</sub>	-	45	60	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switshing Time	ton	-	125	-	no	V <sub>CC</sub> = 10V, I <sub>C</sub> = 4A,
Switching Time	t <sub>OFF</sub>	-	380	-	ns	$I_{B1} = -I_{B2} = 40 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



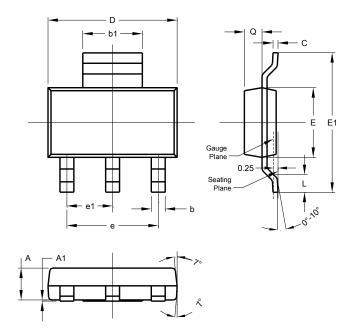
### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





### **Package Outline Dimensions**

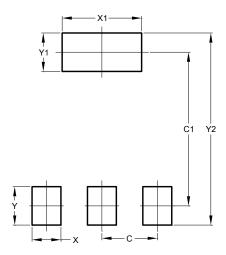
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1			2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)	
С	2.30	
C1	6.40	
Х	1.20	
X1	3.30	
Y	1.60	
Y1	1.60	
Y2	8.00	



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